

Remarks

As an initial matter, to address the objection that the drawings do not show every feature of the claimed invention, the applicant has amended claim 4. Specifically, references to the silicide for S/D and the LDD implantation have been removed from claim 4. Thus, the applicant respectfully requests that the objections to the drawings be withdrawn.

In the Office action, claims 1-8 were rejected as unpatentable over Chong et al. (U.S. Pat. No. 6,727,151) in view of Nishida et al. (U.S. Appl. No. 2003/0151098). By way of the forgoing amendments, claims 1 and 4 have been amended and claim 5 has been cancelled leaving claims 1-4 and 6-8 pending and at issue. In view of the foregoing amendments and the following remarks, reconsideration of the application is respectfully requested.

Independent claim 1 recites a method for fabricating a transistor in a semiconductor device. The method includes etching back the doped poly silicon layer until the pad oxide layer is exposed. This etching forms a doped polysilicon sidewall on a sidewall of the pad nitride layer and the first oxide layer and the doped polysilicon sidewall serves as the lightly doped drain (LDD) implantation.

In contrast, Chong et al. teach that a doped polysilicon sidewall is composed of two doped polysilicon sidewalls 22 and 26 having different doping concentrations. The first sidewall 22 forms a source/drain region and the second sidewall 26 forms a lightly doped source/drain extension to form a MOSFET with an elevated source/drain structure. Thus, in contrast to the doped polysilicon sidewall recited in claim 1, which serves as the LDD implantation, the sidewall structure taught by Chong et al. requires two sidewall structures that have different doping concentrations. Nishida et al. fails to overcome the above-noted deficiency of Chong et al. Consequently, it is submitted that independent claim 1 and all claims dependent thereon are in condition for allowance.

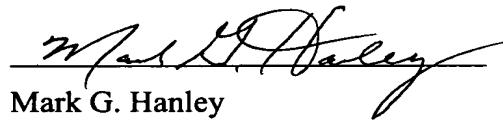
CONCLUSION

For at least the foregoing reasons, the applicant now respectfully submits that all of the pending claims are in condition for allowance. Accordingly, it is respectfully requested that the outstanding rejections be withdrawn and that claims 1-4 and 6-8 be allowed.

Reconsideration of the application and allowance thereof are respectfully requested. If there is any matter that the examiner would like to discuss, the examiner is invited to contact the undersigned representative at the telephone number set forth below.

Respectfully submitted,
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